NPN RF Transistor
(continued)

Electrical Characteristics
TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHARACTERISTICS					
$V_{CEO(sus)}$	Collector-Emitter Sustaining Voltage*	I_C = 3.0 mA, I_B = 0	12		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C = 1.0 µA, I_E = 0	20		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E = 10 µA, I_C = 0	2.5		V
I_{CBO}	Collector Cutoff Current	V_{CB} = 15 V, I_E = 0 V_{CB} = 15 V, T_A = 150°C		0.02 1.0	µA µA
ON CHARACTERISTICS					
h_{FE}	DC Current Gain	I_C = 3.0 mA, V_{CE} = 1.0 V	25	250	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C = 10 mA, I_B = 1.0 mA		0.4	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C = 10 mA, I_B = 1.0 mA		1.0	V
SMALL SIGNAL CHARACTERISTICS					
f_T	Current Gain - Bandwidth Product	I_C = 5.0 mA, V_{CE} = 6.0 V, f = 100 MHz	900	2000	MHz
C_{cb}	Collector-Base Capacitance	V_{CB} = 10 V, I_E = 0, f = 0.1 to 1.0 MHz		1.0	pF
h_{fe}	Small-Signal Current Gain	I_C = 2.0 mA, V_{CE} = 6.0 V, f = 1.0 kHz	25	300	
$rb'C_c$	Collector Base Time Constant	I_C = 2.0 mA, V_{CB} = 6.0 V, f = 31.9 MHz	3.0	14	ps
NF	Noise Figure	I_C = 1.5 mA, V_{CE} = 6.0 V, R_S = 50Ω, f = 200 MHz		5.0	dB
FUNCTIONAL TEST					
G_{pe}	Amplifier Power Gain	V_{CE} = 6.0 V, I_C = 5.0 mA, f = 200 MHz	15		dB
P_O	Power Output	V_{CB} = 10 V, I_E = 12 mA, f ≥ 500 MHz	20		mW

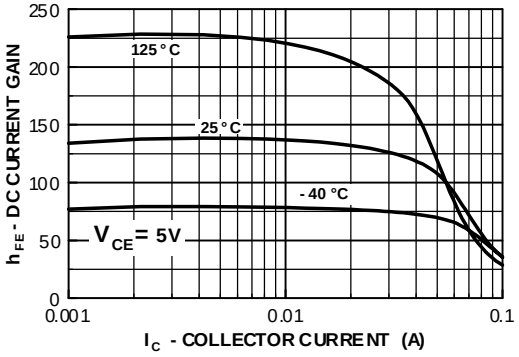
*Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2.0%

Spice Model

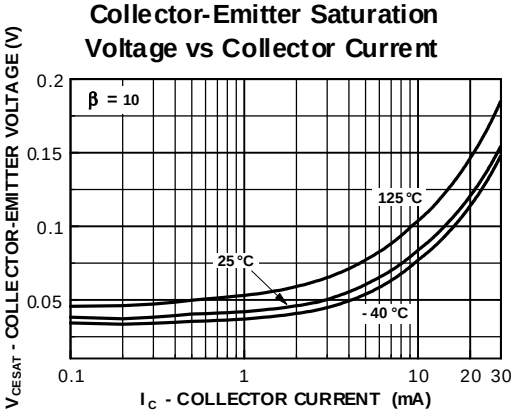
NPN (Is=69.28E-18 Xti=3 Eg=1.11 Vaf=100 Bf=282.1 Ne=1.177 Ise=69.28E-18 Ikf=22.03m Xtb=1.5 Br=1.176 Nc=2 Isc=0 Ikr=0 Rc=4 Cjc=1.042p Mjc=.2468 Vjc=.75 Fc=.5 Cje=1.52p Mje=.3223 Vje=.75 Tr=1.588n Tf=135.6p Itf=.27 Vtf=10 Xtf=30 Rb=10)

Typical Characteristics

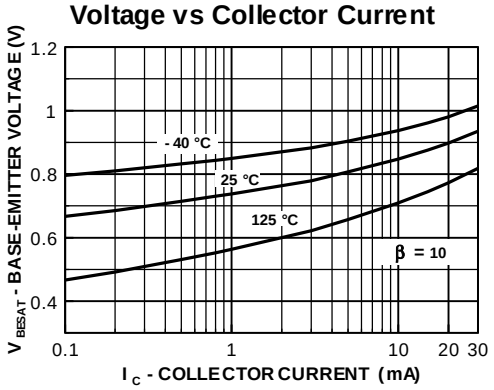
DC Current Gain vs Collector Current



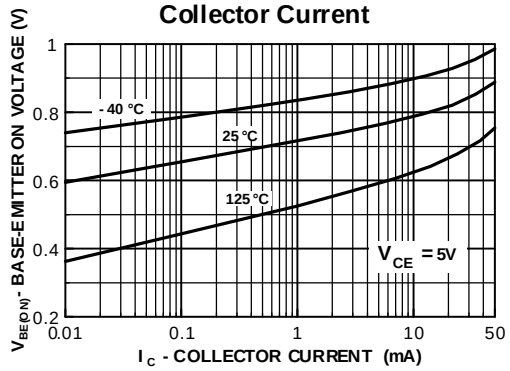
Collector-Emitter Saturation Voltage vs Collector Current



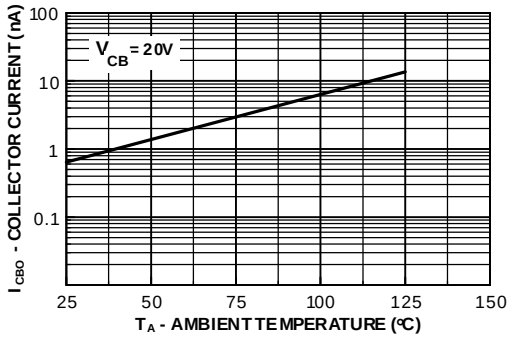
Base-Emitter Saturation Voltage vs Collector Current



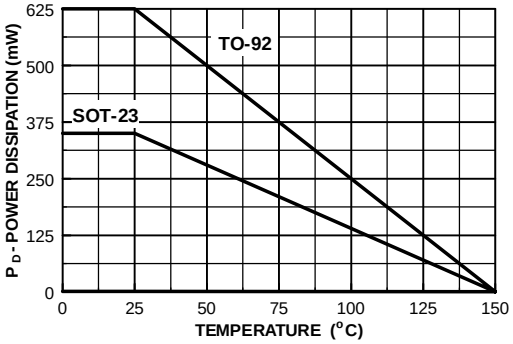
Base-Emitter ON Voltage vs Collector Current



Collector-Cutoff Current vs Ambient Temperature



Power Dissipation vs Ambient Temperature



Test Circuit

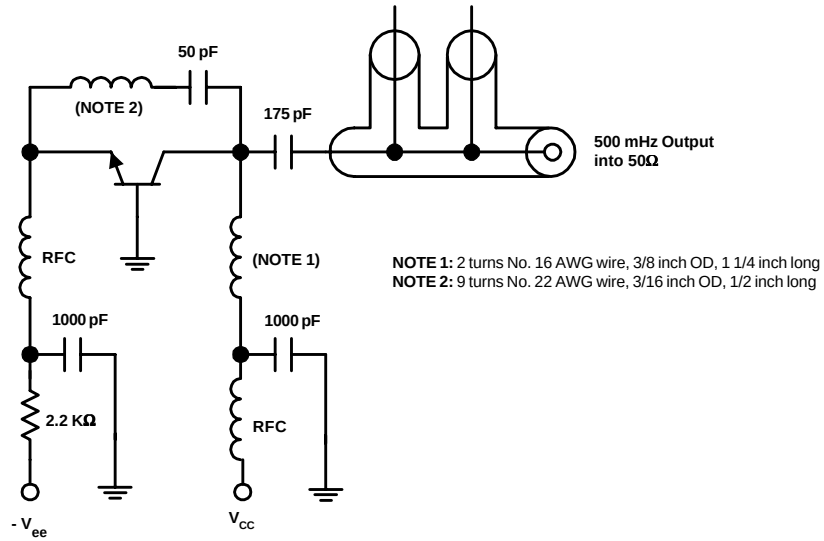
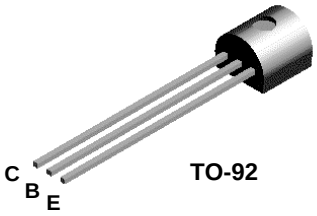


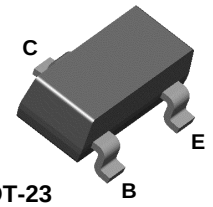
FIGURE 1: 500 MHz Oscillator Circuit

FAIRCHILD
SEMICONDUCTOR TM

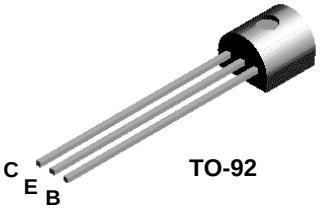
MPS5179 MMBT5179 PN5179



TO-92



SOT-23
Mark: 3C



TO-92

NPN RF Transistor

This device is designed for use in low noise UHF/VHF amplifiers with collector currents in the 100 μA to 30 mA range in common emitter or common base mode of operation, and in low frequency drift, high ouput UHF oscillators. Sourced from Process 40.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	12	V
V_{CBO}	Collector-Base Voltage	20	V
V_{EBO}	Emitter-Base Voltage	2.5	V
I_C	Collector Current - Continuous	50	mA
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:
1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units
		PN/MPS5179	*MMBT5179	
P_D	Total Device Dissipation Derate above 25°C	350 2.8	225 1.8	mW mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	556	°C/W

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

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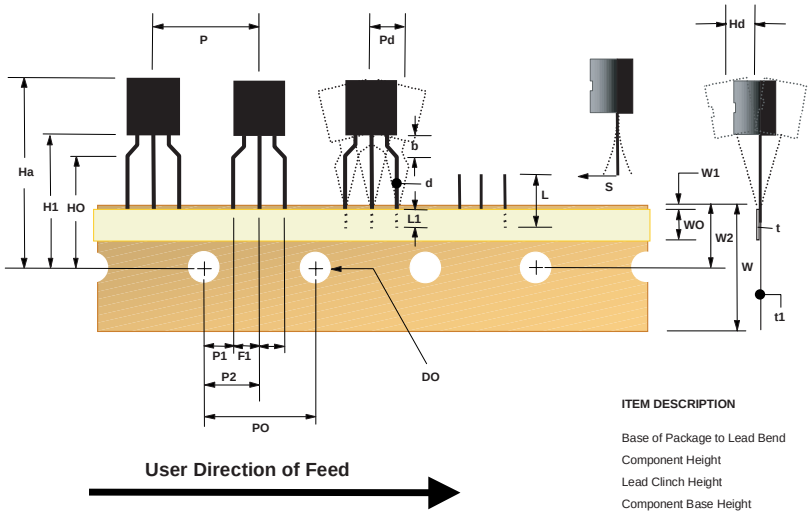
TO-92 Tape and Reel Data, continued

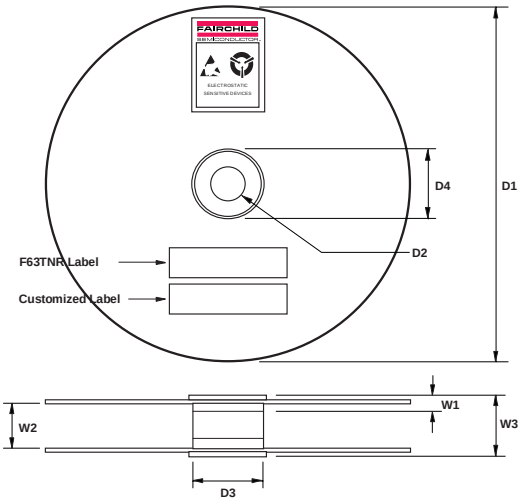
TO-92 Tape and Reel Taping
Dimension Configuration: Figure 4.0



ITEM DESCRIPTION	SYMBOL	DIMENSION
Base of Package to Lead Bend	b	0.098 (max)
Component Height	Ha	0.928 (+/- 0.025)
Lead Clinch Height	HO	0.630 (+/- 0.020)
Component Base Height	H1	0.748 (+/- 0.020)
Component Alignment (side/side)	Pd	0.040 (max)
Component Alignment (front/back)	Hd	0.031 (max)
Component Pitch	P	0.500 (+/- 0.020)
Feed Hole Pitch	PO	0.500 (+/- 0.008)
Hole Center to First Lead	P1	0.150 (+0.009, -0.010)
Hole Center to Component Center	P2	0.247 (+/- 0.007)
Lead Spread	F1/F2	0.104 (+/- 0 .010)
Lead Thickness	d	0.018 (+0.002, -0.003)
Cut Lead Length	L	0.429 (max)
Taped Lead Length	L1	0.209 (+0.051, -0.052)
Taped Lead Thickness	t	0.032 (+/- 0.006)
Carrier Tape Thickness	t1	0.021 (+/- 0.006)
Carrier Tape Width	W	0.708 (+0.020, -0.019)
Hold - down Tape Width	WO	0.236 (+/- 0.012)
Hold - down Tape position	W1	0.035 (max)
Feed Hole Position	W2	0.360 (+/- 0.025)
Sprocket Hole Diameter	DO	0.157 (+0.008, -0.007)
Lead Spring Out	S	0.004 (max)

Note : All dimensions are in inches.

TO-92 Reel
Configuration: Figure 5.0



ITEM DESCRIPTION	SYSMBOL	MINIMUM	MAXIMUM
Reel Diameter	D1	13.975	14.025
Arbor Hole Diameter (Standard)	D2	1.160	1.200
(Small Hole)	D2	0.650	0.700
Core Diameter	D3	3.100	3.300
Hub Recess Inner Diameter	D4	2.700	3.100
Hub Recess Depth	W1	0.370	0.570
Flange to Flange Inner Width	W2	1.630	1.690
Hub to Hub Center Width	W3		2.090

Note: All dimensions are inches